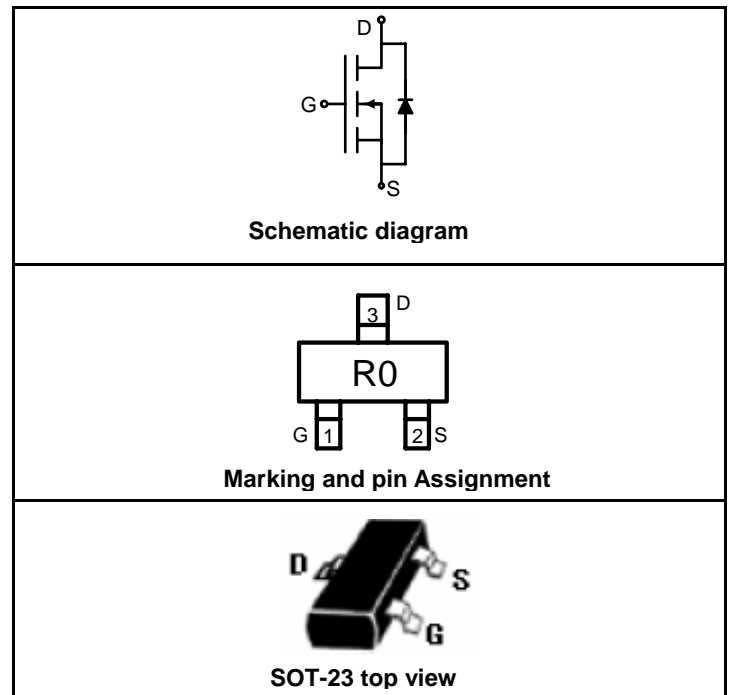


## N-Channel Enhancement Mode Field Effect Transistor

### FEATURE

- High dense cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability



### Maximum ratings ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	5.8	A
Drain Current-Pulsed (note 1)	$I_{DM}$	30	A
Maximum Power Dissipation	$P_D$	1.38	W
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	90	$^{\circ}\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55~+150	$^{\circ}\text{C}$

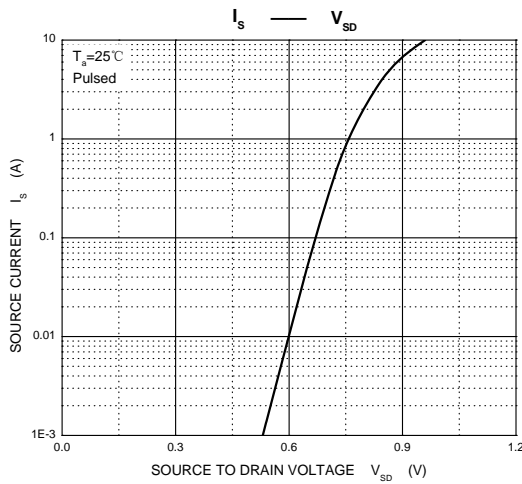
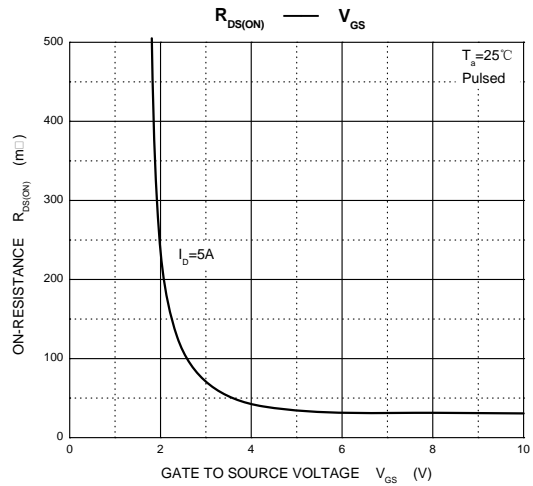
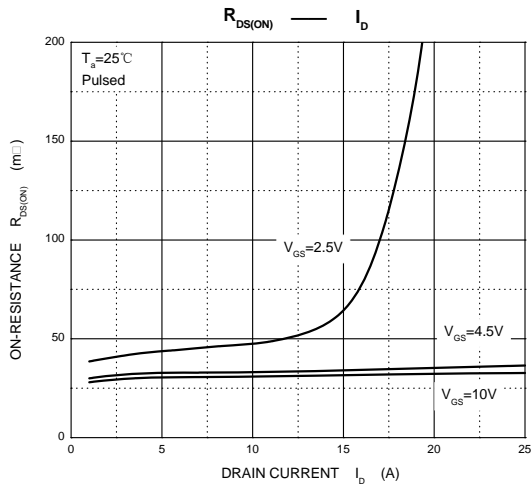
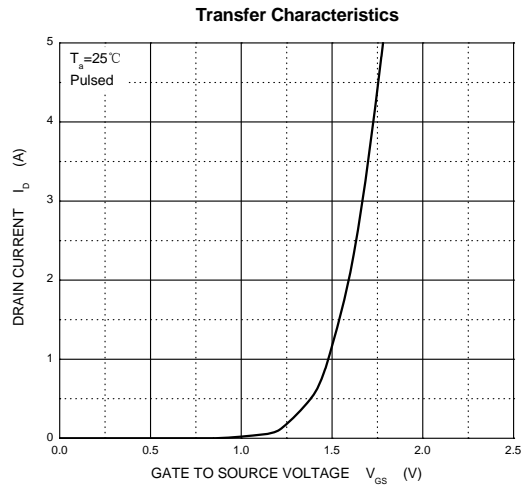
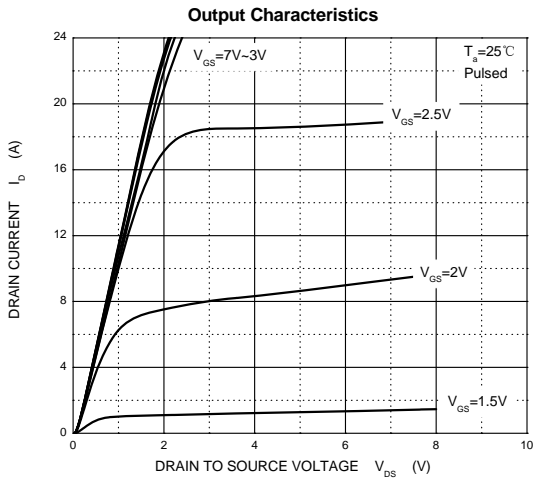
## Electrical characteristics ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 24V, V_{GS} = 0V$			1	$\mu A$
Gate-source leakage current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0V$			$\pm 100$	nA
<b>On characteristics</b>						
Drain-source on-resistance (note 3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5.8A$			35	m $\Omega$
		$V_{GS} = 4.5V, I_D = 5A$			40	m $\Omega$
		$V_{GS} = 2.5V, I_D = 4A$			52	m $\Omega$
Forward transconductance	$g_{FS}$	$V_{DS} = 5V, I_D = 5A$	8			S
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.7		1.4	V
<b>Dynamic Characteristics (note 4,5)</b>						
Input capacitance	$C_{iss}$	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$			1050	pF
Output capacitance	$C_{oss}$			99		pF
Reverse transfer capacitance	$C_{rss}$			77		pF
Gate resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$			3.6	$\Omega$
<b>Switching Characteristics (note 4,5)</b>						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 15V,$ $R_L = 2.7\Omega, R_{GEN} = 3\Omega$			5	ns
Turn-on rise time	$t_r$				7	ns
Turn-off delay time	$t_{d(off)}$				40	ns
Turn-off fall time	$t_f$				6	ns
<b>Drain-source diode characteristics and maximum ratings</b>						
Diode forward voltage (note 3)	$V_{SD}$	$I_S = 1A, V_{GS} = 0V$			1	V

### Note :

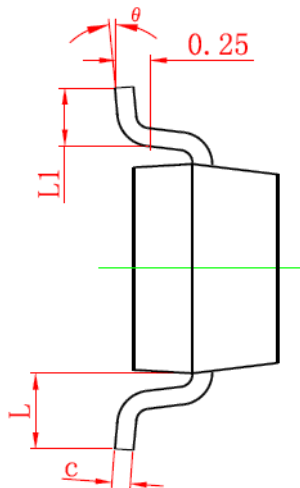
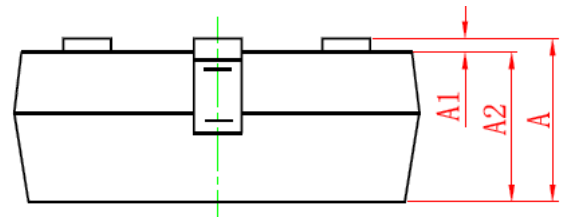
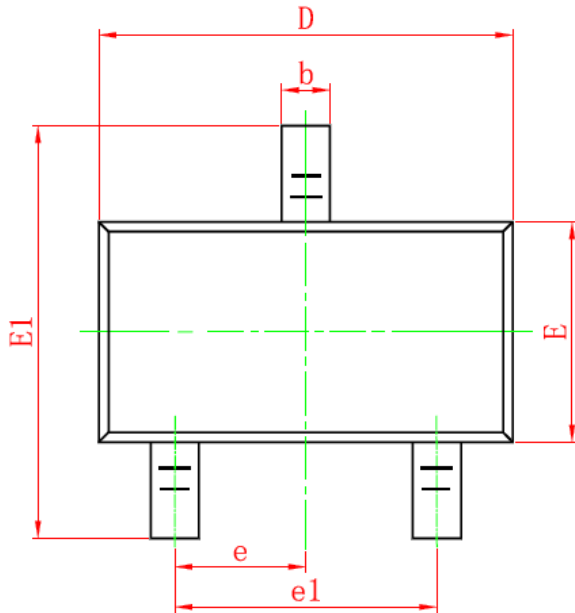
1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t < 5$  sec.
3. Pulse Test : Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing.

## Typical Characteristics



## SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
$\theta$	0°	8°

### NOTES

- All dimensions are in millimeters.
- Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
- Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- Dimension L is measured in gauge plane.
- Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.